

# YJ Planar Schottky Barrier Diode Die Specification

150V 20A, 108mil, Schottky barrier diode die based on silicon planar process  
Part No.: PSB108H150AS-280A

## Main Products Characterstics

### Maximum Ratings

### Static Electrical Characteristics (Ta = 25°C)

$I_F = 20\text{ A}$

$\leq 2\%$

## Device Schematics and Outline Drawing

- Die Thickness \*
- Die Size \*\*
- Top Metal Pad
- Active Area
- Top Metal
- Back Metal
- Note: 1 \* : Also can offer device with 8 mils thickness
- 2 \*\*: Cutting street width is around 1.5 mils

## Important Notice

Specification apply to die only. Actual performance may degrade when assembled.

Recommended Storage Environmen\*(is) BDC5160003.76 reWBtWnBTWnBTW